Supporting Information of

Ni(NCS)₂ monolayer: a robust bipolar magnetic semiconductor

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1. Variation of magnetic moment and energy difference with U value

Figure S1 The changes of magnetic moment (a) and energy difference of U (b) in the range 1-7 respectively.

Only using the method of PBE will ignore some interrelated effects of electrons. Especially for transition metal elements, which have 3d orbits, the method of Hubbard Coulomb interaction U should be deemed to improve the accuracy of calculation. So, the Ni atom, in the calculation process, adopts the method of PBE+U to deal with the strongly correlated system. In order to better find out the appropriate U, we also tested the U theoretically. The Ni(NCS)₂ monolayer maintains the ferromagnetic ground state regardless of how the U value is varied from 1 to 7. The magnetic moment on single Ni increases linearly with the increase of U value (as shown in Figure S1a). Not only that, but the variation of E with U is also interesting. When U value is between 1 and 4, the value of E decreases rapidly; as U exceeds 4 and increases, E value decreases gradually, and finally the curve tends to be smooth (as shown in Figure S1b). Therefore, we decide to use U = 4 to calculate the properties of the Ni(NCS)₂ monolayer. Besides, the lattice parameters of bulk after relaxation (under $U_{\text{eff}} = 4 \text{ eV}$) is a = 10.6115 Å, b = 3.6728 Å, c = 6.1614 Å, respectively, which in good agreement with the experimental values (a = 10.5070 Å, b = 3.6189 Å, c = 6.1625 Å)¹. Therefore $U_{\text{eff}} = 4.0 \text{ eV}$ is adopted within the GGA+U calculations.

2. The detailed structural information of bulk and monolayer $Ni(NCS)_2$ after relaxation.

The POSCAR of bulk Ni ₂ C ₄ S ₄ N ₄		
1.0	0.0000000000000000000000000000000000000	0.0106287400222404
0.0000000000000000000000000000000000000	2 6728540254677425	0.0190387409333494
1 7102150778450240	0.0000000000000000000000000000000000000	6 3864250467001405
-1./102130//6430249	0.0000000000000000000000000000000000000	0.3804230407001493
$\frac{1}{2} \frac{1}{4} \frac{1}{4} \frac{1}{4}$		
2 + + + Direct		
	0.0000000000000000000000000000000000000	0.00000000000000000
0.5000000000000000000000000000000000000	0.5000000000000000000000000000000000000	0.0000000000000000000000000000000000000
0.7638007610075661	0.0000000000000000000000000000000000000	0.1977532968400766
0.7361997389974339	0.5000000000000000000000000000000000000	0.8022466731599280
0.2638007610075661	0.5000000000000000000000000000000000000	0 1977532968400766
0.2361992249924398	0.0000000000000000000000000000000000000	0.8022466731599280
0.8823548581731515	0.5000000000000000000000000000000000000	0.7630816523888697
0.6176451418268485	0.0000000000000000000000000000000000000	0.2369183176111349
0 3823548581731515	0.0000000000000000000000000000000000000	0.7630816523888697
0 1176451418268485	0.500000000000000000	0 2369183176111349
0.8646660479561135	0.0000000000000000000000000000000000000	0 1535597731076734
0.6353339520438865	0.500000000000000000	0.8464402268923266
0.3646660479561135	0.50000000000000000	0.1535597731076734
0.1353339520438865	0.00000000000000000	0.8464402268923266
The POSCAR of monolay	$\operatorname{ver} N_{12}C_4S_4N_4$	
1.0	0.0000000000000000000000000000000000000	0.0000000000000000000000000000000000000
10.490432881353781	0.00000000000000000	0.0000000000000000000000000000000000000
0.00000000000000000	3./19/955245153338	
0.000000000000000000000000000000000000	0.0000000000000000000000000000000000000	30.000000000000000000000000000000000000
$\frac{1}{2}$		
2444 Direct		
	0.0000000000000000000000000000000000000	0 6250400780000078
0.0000000000000000000000000000000000000	0.0000000000000000000000000000000000000	0.02394997899999978
0.8301252520022050	0.0000000000000000000000000000000000000	0.02394997899999978
0.8591252520022050	0.0000000000000000000000000000000000000	0.6587002546726625
0.5591252520022050	0.0000000000000000000000000000000000000	0.0387005340750023
0.1008/4/3399/8009	0.0000000000000000000000000000000000000	0.5951890495205409
0.5755375630262501	0.0000000000000000000000000000000000000	0.5751670495205409
0.0755375850262530	0.0000000000000000000000000000000000000	0.6765773135955300
0.0755575850202559	0.0000000000000000000000000000000000000	0.5753126804044608
0.9244624369737409	0.5000000000000000000000000000000000000	0 5753126894044698
0.7244024309737409		0.6666363018586504
0.7294223001429373	0.5000000000000000000000000000000000000	0 6666363018586594
0 2705776118570427	0.0000000000000000000000000000000000000	0 5852537021413369
0.7705776110570427	0.500000000000000000000000000000000000	0 5953537031412260
0.//03//01183/042/	0.0000000000000000000000000000000000000	0.303233/021413309

3. The different magnetic configurations of ferromagnetic (FM) and antiferromagnetic (AFM) for Ni(NCS)₂ monolayer.



Figure S2 The different magnetic configurations of Ni(NCS)₂ monolayer

Based on the calculated total energies of different magnetic configurations (Figure S2) and normalized S(|S| = 1), the exchange parameters J_1 and J_2 can be derived by following equations: $E_{EM} = E_0 - (J_1 + 2J_2)|S|^2 - A|S|^2$ (1)

$$E_{AFM1} = E_0 - (-J_1)|S|^2 - A|S|^2 \quad (3)$$
$$E_{AFM2} = E_0 - (J_1 - 2J_2)|S|^2 - A|S|^2 \quad (3)$$

 E_0 is the total energy excluding the magnetic coupling (not sensitive to different magnetic states). For, anisotropy energy parameter A, spin-orbital coupling (SOC) calculations are performed on 2D Ni(NCS)₂ monolayer crystal to obtain the relative stability along three magnetization directions in plane, that is (100), (010), and (001) direction. A is calculated to be -415 μeV by using the magnetic anisotropy energies as below:

$$A = \frac{E(100) - E(001)}{|S|^2}$$

4. The Poisson's ratio (v) and the in-plane Young's modulus



Figure S3 Calculated orientation-dependent Poisson's ratio (a), and Young's modulus (b).

The Poisson's ratio and the in-plane Young's modulus can represent the elastic properties of 2D materials, which were plotted based on the calculated elastic constants (Figure S3). The calculated the Poisson's ratios along x- and y-axis for the Ni(NCS)₂ monolayer are 0.30 and 0.082, respectively, suggesting its high anisotropy in space. For Young's modulus of Ni(NCS)₂ monolayer the maximum value is 85.9 N/m along x-axis, which is comparable with that of silicene

(61 N/m) and a litter lower than that of MoS_2 monolayer (123 N/m). The result also reveals strong anisotropy of Ni(NCS)₂ monolayer.



5. Electronic structure of Ni(NCS)₂ monolayer.

Figure S4 The orbital-projected density of states of the Ni_d orbit calculated under the PBE+U(a) and HSE06 (b) methods. The orbital-projected density of states of the t_{2g} orbit and e_g orbit calculated under the PBE+U(c) and HSE06 (d) methods.



Figure S5 (a) The spin charge density distribution of $Ni(NCS)_2$ monolayer with the isosurface value of 0.002 e/bohr³. Yellow represents spin-up and blue represents spin-down. (b) Octahedral crystal of hex-coordinated Ni atom.

6. Under the applied strain and doping, the magnetic moment change and band structures of Ni(NCS)₂ monolayer.



Figure S6 Band structure of Ni(NCS)₂ monolayer under compressive strain.



Figure S7 Band structure of Ni(NCS)₂ monolayer under tensile strain.

Figure S6 shows that the band gap becomes smaller with the application of a stretching -1% to -3% compressive strain whether it is uniaxial or biaxial compressive strains. Figure S7 demonstrates that a larger band gap can be obtained with tensile strain and the band gaps increases as the tensile strain increases (from 1% to 3%). This result shows tunable band gaps of Ni(NCS)₂ monolayer.



Figure S8 Changes of magnetic moment under different strain (x-axis (a), y-axis (b), and xy-axis (c)) and doping (d).



Figure S9 Band structures of doping with two holes (a), one hole (b), two electrons (c), and one electron (d), respectively.

References

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